

## Product Summary

$BV_{DSS}$	$R_{DS(ON)}$	$I_D$ $T_A = +25^\circ C$
50V	2.0Ω @ $V_{GS} = 5.0V$	300mA
	2.5Ω @ $V_{GS} = 2.5V$	200mA

## Features and Benefits

- Low On-Resistance
- Very Low Gate Threshold Voltage (1.0V max)
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

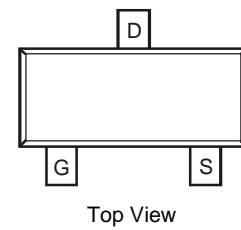
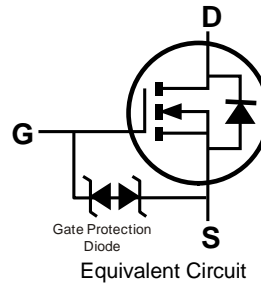
## Description and Applications

This new generation 50V N-channel enhancement mode MOSFET is designed to minimize  $R_{DS(on)}$  yet maintain superior switching performance. This device is ideal for use in notebook battery power management and load switch.

- Load Switches
- Level Switches

## Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.  
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Alloy 42 Leadframe.  
Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

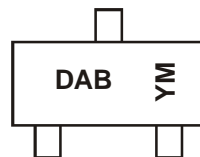


## Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
DMN5L06K-7	Commercial	SOT23	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



DAB = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: G = 2019)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2006	~	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	T	~	G	H	I	J	K	L	M	N	O	P
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	$V_{DSS}$	50	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Drain Current (Note 5)	$I_D$	Continuous	300
		Pulsed (Note 6)	800

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_D$	350	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-65 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	50	—	—	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	60	nA	$V_{DS} = 50V, V_{GS} = 0V$
Gate-Body Leakage	$I_{GSS}$	—	—	1	$\mu A$	$V_{GS} = \pm 12V, V_{DS} = 0V$
				500	nA	$V_{GS} = \pm 10V, V_{DS} = 0V$
				50	nA	$V_{GS} = \pm 5V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	0.49	—	1.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	—	3.0	$\Omega$	$V_{GS} = 1.8V, I_D = 50mA$
		—	—	2.5		$V_{GS} = 2.5V, I_D = 50mA$
		—	—	2.0		$V_{GS} = 5.0V, I_D = 50mA$
On-State Drain Current	$I_{D(on)}$	0.5	1.4	—	A	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance	$ Y_{fs} $	200	—	—	mS	$V_{DS} = 10V, I_D = 0.2A$
Source-Drain Diode Forward Voltage	$V_{SD}$	0.5	—	1.4	V	$V_{GS} = 0V, I_S = 115mA$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{iss}$	—	—	50	pF	$V_{DS} = 25V, V_{GS} = 0V$ $f = 1.0MHz$
Output Capacitance	$C_{oss}$	—	—	25	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	—	5.0	pF	

- Notes:
- Device mounted on FR-4 PCB
  - Pulse width  $\leq 10ms$ , Duty Cycle  $\leq 1\%$ .
  - Short duration pulse test used to minimize self-heating effect.

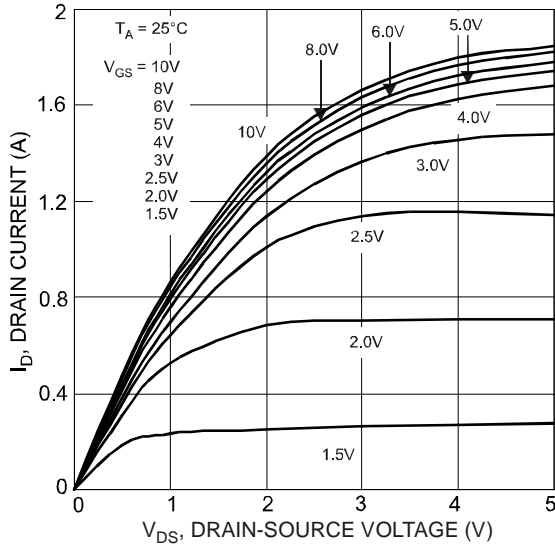


Fig. 1 Typical Output Characteristics

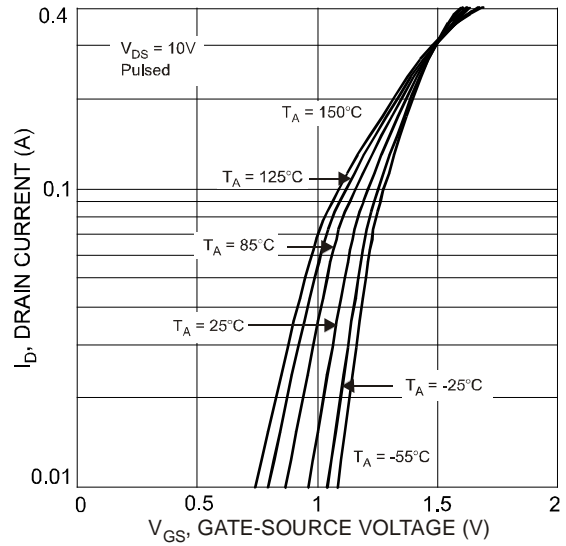


Fig. 2 Typical Transfer Characteristics

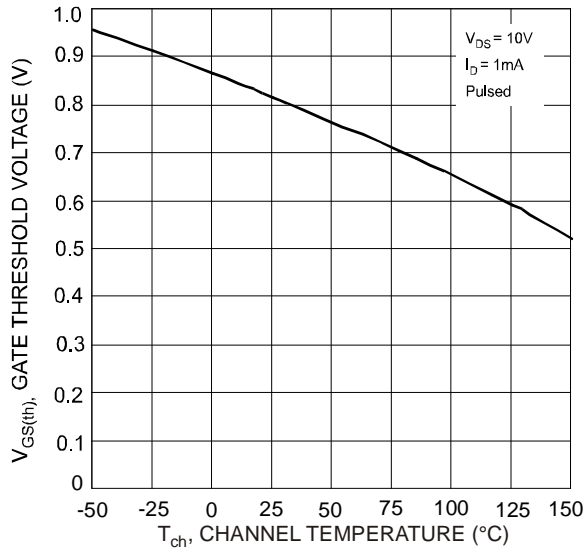


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

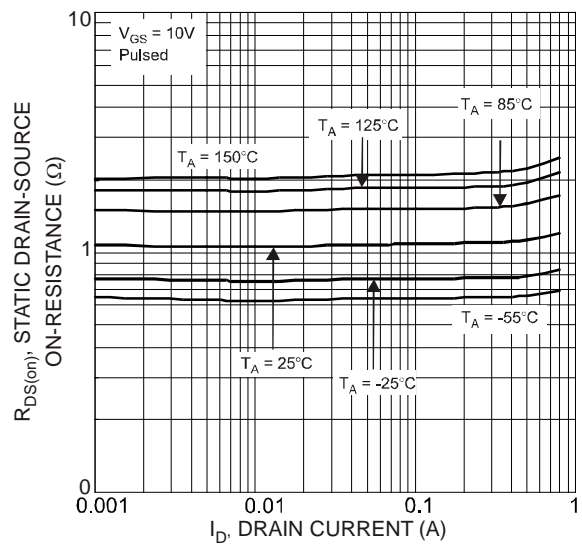


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

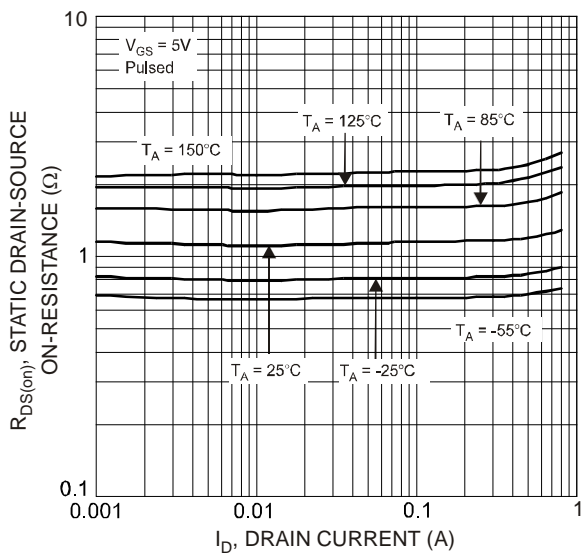


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

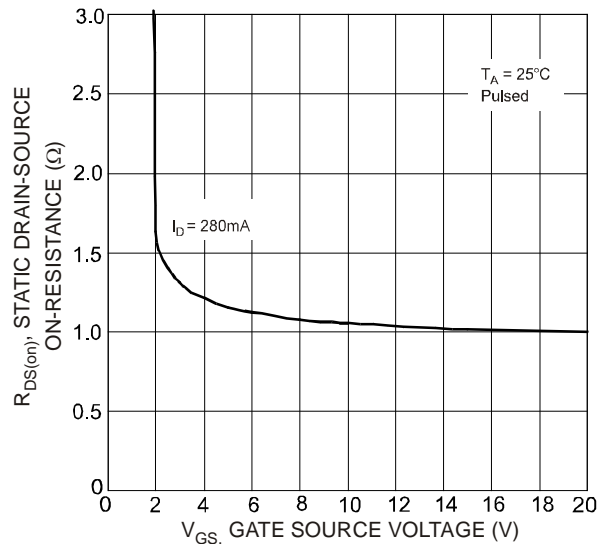


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

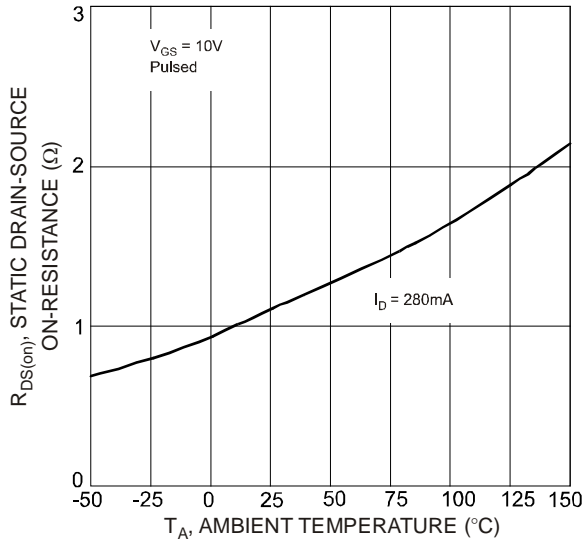


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

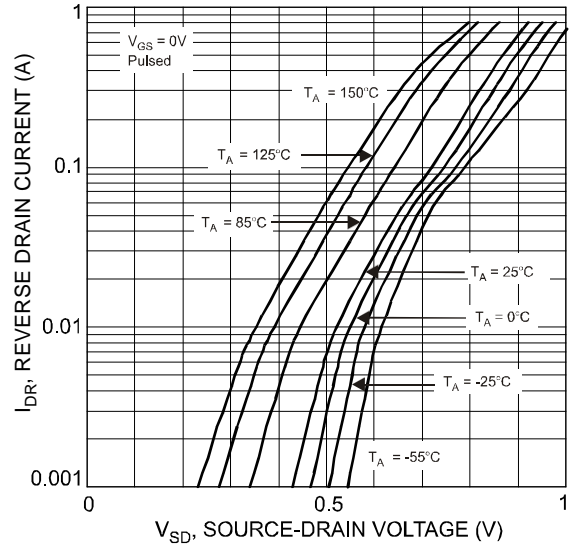


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

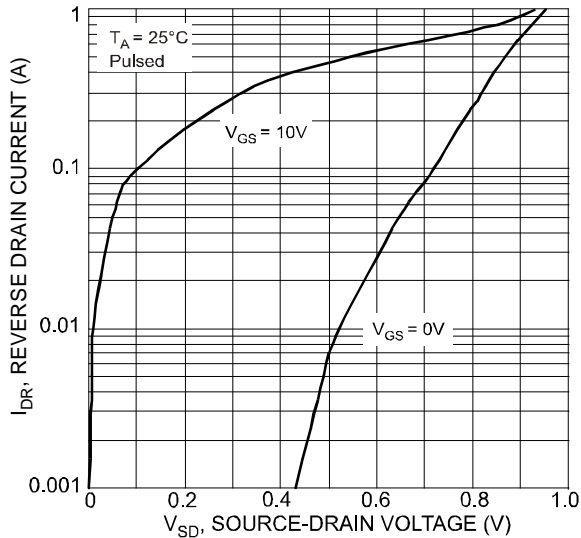


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

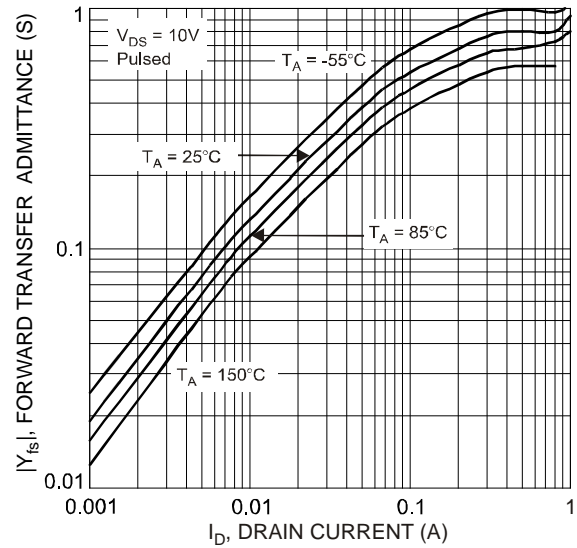


Fig. 10 Forward Transfer Admittance vs. Drain Current

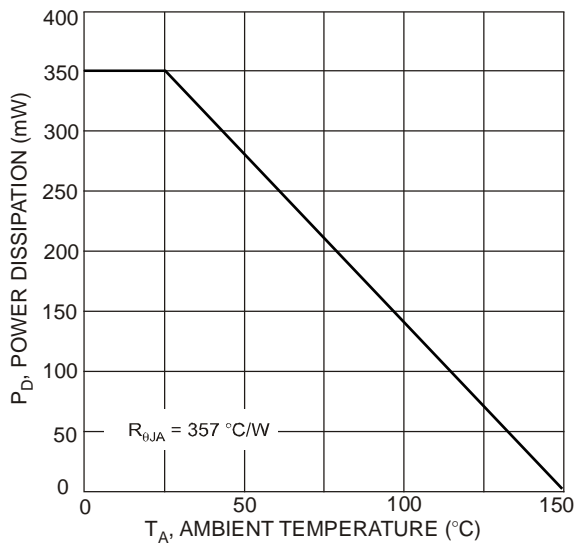


Fig. 11 Derating Curve - Total

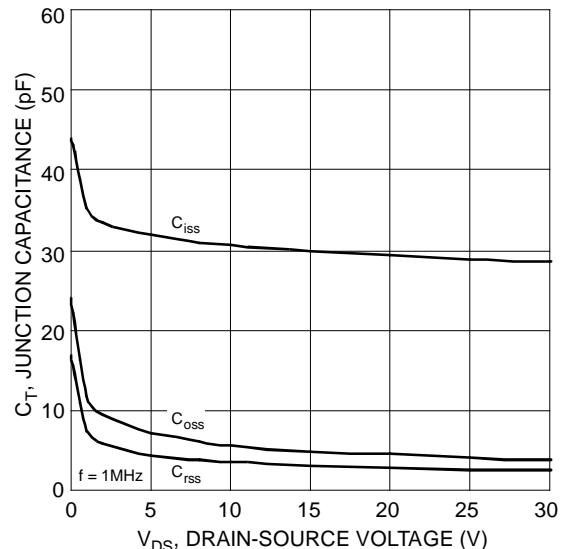
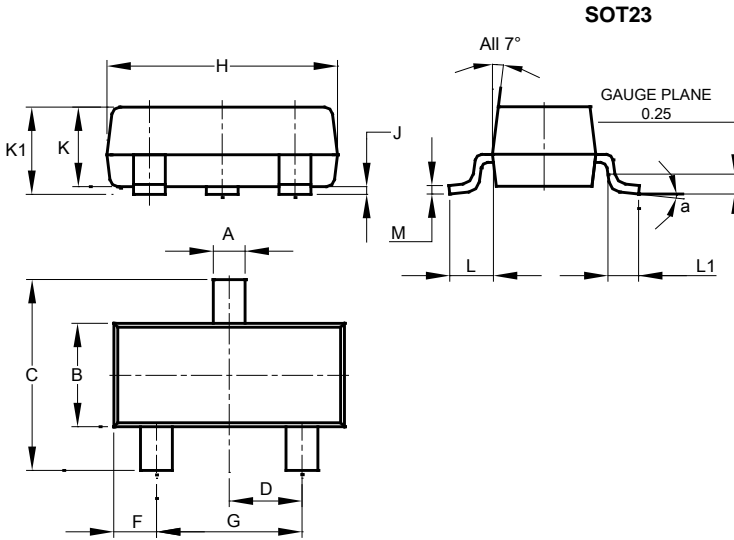


Figure 12 Typical Junction Capacitance

**Package Outline Dimensions**

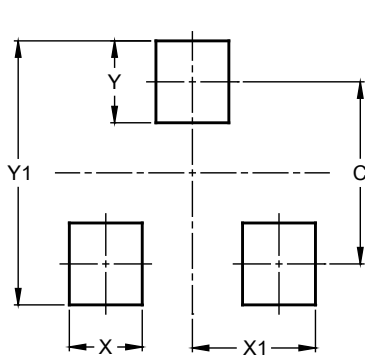
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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